

PUMD24-Q

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

28 May 2024

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- · Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Low current peripheral driver
- Control of IC inputs
- · Replacement of general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	20	mA
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[2]	0.8	1	1.2	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PUMD24-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD24-Q	Т8%

[1] % = placeholder for manufacturing site code

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

8. Limiting values

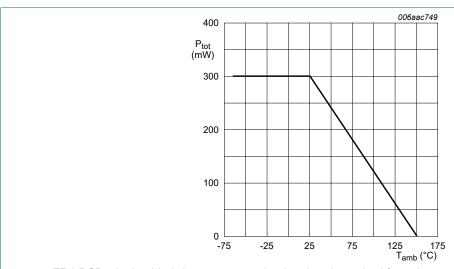
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or			'		
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V _{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V _{EBO}	emitter-base voltage	open collector	[1]	-	10	V
V _I	input voltage	input voltage TR1		-10	40	V
		input voltage TR2		-40	10	V
Io	output current		[1]	-	20	mA
I _{CM}	peak collector current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

For the PNP transistor with negative polarity.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

PUMD24-Q

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50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

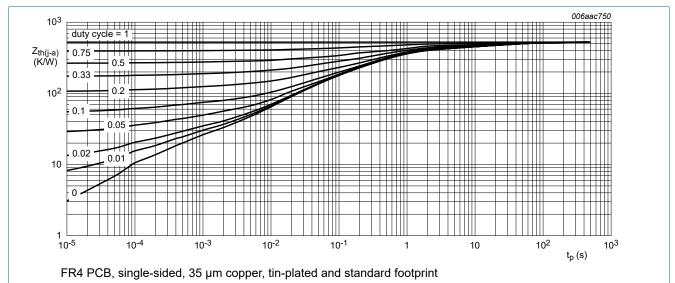


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

10. Characteristics

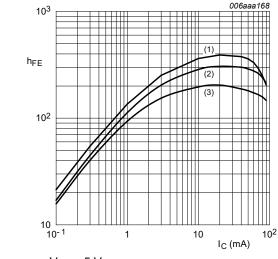
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	[1]	-	-	5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	[1]	-	-	50	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 20 mA; T _{amb} = 25 °C	[1]	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	1.1	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	3	1.5	-	V
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[2]	0.8	1	1.2	
TR1 (NPN)						_	
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
TR2 (PNP)							
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF

^[1] For the PNP transistor with negative polarity.

^[2] See section "Test information" for resistor calculation and test conditions.

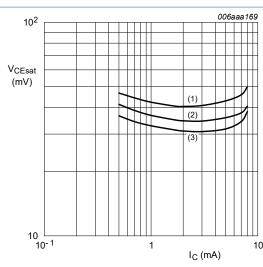
50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω



 $V_{CE} = 5 V$ (1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

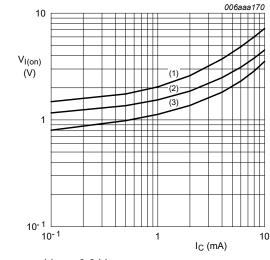
TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



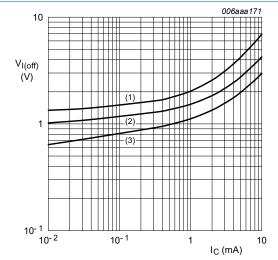
 V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$

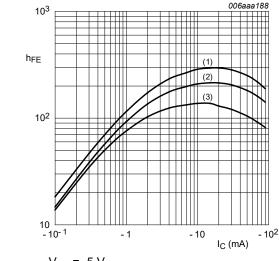
(1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

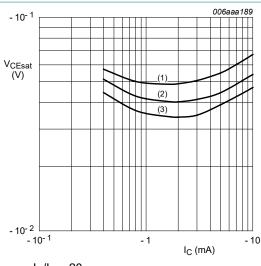


$$V_{CE}$$
 = -5 V

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

TR2 (PNP): DC current gain as a function of Fig. 7. collector current; typical values

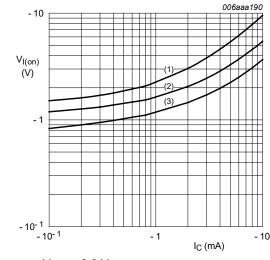


$$I_{\rm C}/I_{\rm B}=20$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 8. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



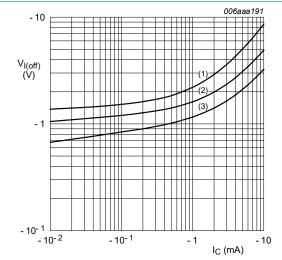
$$V_{CE} = -0.3 V$$

$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 9. of collector current; typical values



$$V_{CE}$$
 = -5 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

TR2 (PNP): On-state input voltage as a function | Fig. 10. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

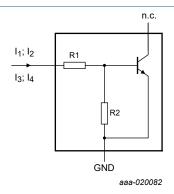


Fig. 11. TR1 (NPN): Resistor test circuit

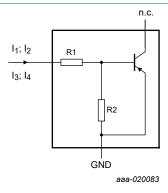


Fig. 12. TR2 (PNP): Resistor test circuit

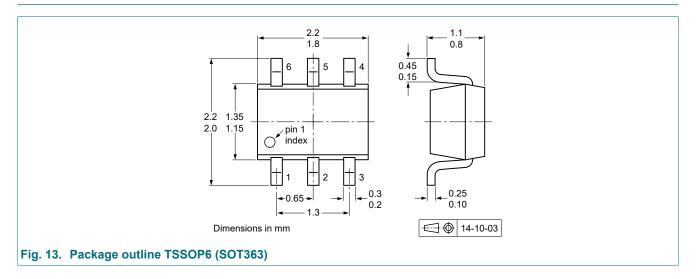
Resistor test conditions

Table 8. Resistor test conditions

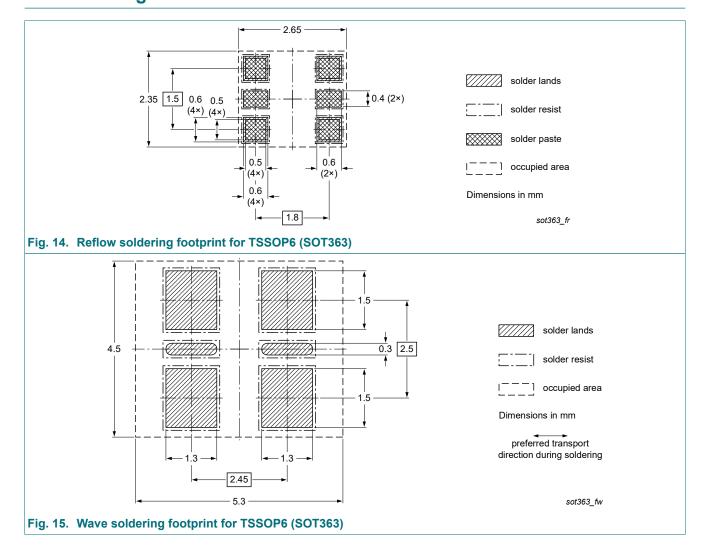
PUMD24	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	l ₃	I ₄	
TR1 (NPN)	100	100	20 μΑ	60 μΑ	-20 μA	-40 μA	
TR2 (PNP)	100	100	-20 µA	-60 µA	20 μΑ	40 μA	

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 kΩ, R2 = 100 kΩ

12. Package outline



13. Soldering



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD24-Q v.1	20240528	Product data sheet	-	-

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PUMD24-C

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

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